

ABSTRACT

A planar body of an oxide single crystal having a good crystallinity is grown stably to prevent cracks in the crystal, when the planar body of the oxide single crystal is grown with a μ pulling-down method. A raw material of the oxide single crystal is melted in a crucible 7. A seed crystal 15 is contacted to a melt 8. An oxide single crystal 31 is grown by pulling down the seed crystal 15 to draw the melt from an opening 13c of the crucible 7. A cooler is provided under the opening 13c of the crucible 7, which cool the oxide single crystal drawn from the opening of the crucible.